TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12G45, SM12J45, SM12G45A, SM12J45A

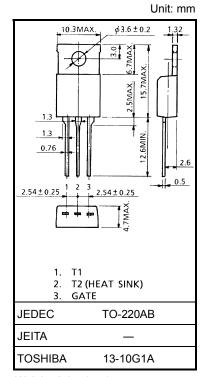
AC POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
 R.M.S On-State Current : IT (RMS) = 12A

• High Commutating (dv / dt)

MAXIMUM RATINGS

CHARACTERIS	SYMBOL	RATING	UNIT		
Repetitive Peak	SM12G45 SM12G45A	V _{DRM}	400	V	
Off-State Voltage	SM12J45 SM12J45A	V DRM	600		
R.M.S On-State Current (Full Sine Waveform Tc =	I _{T (RMS)}	12	А		
Peak One Cycle Surge On-State Current (Non-Repetitive)		I	120 (50Hz)	А	
		I _{TSM}	132 (60Hz)		
I ² t Limit Value (t = 1~10m	I ² t	72	A ² s		
Critical Rate of Rise of O Current	di / dt	50	A / µs		
Peak Gate Power Dissipa	P_{GM}	5	W		
Average Gate Power Disa	P _G (AV)	0.5	W		
Peak Gate Voltage	V_{GM}	10	V		
Peak Gate Current	I _{GM}	2	Α		
Junction Temperature	Tj	-40~125	°C		
Storage Temperature Ra	T _{stg}	-40~125	°C		



Weight: 2.0 g (typ.)

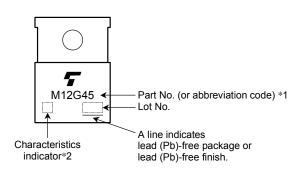


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

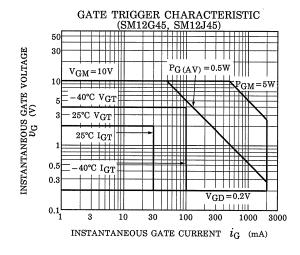
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} =Rated, T _j = 125°C		_	_	2	mA		
Gate Trigger Voltage			- 1	V _{GT}	V _D = 12V, R _L = 20Ω	T2 (+) , Gate (+)		_	2	V
	SM12	2G45	II			T2 (+) , Gate (-)	_	_	2	
	SM12	SM12J45	III			T2 (-) , Gate (-)		_	2	
			IV			T2 (-) , Gate (+)	_	_	_	
			- 1			T2 (+) , Gate (+)	_	_	1.5	
		2G45A	Ш			T2 (+) , Gate (-)	_	_	1.5	
	SM12	2J45A	III			T2 (-) , Gate (-)	_	_	1.5	
			IV			T2 (-) , Gate (+)	I	_		
Gate Trigger Current Si			- 1	lgt	V _D = 12V, R _L = 20Ω	T2 (+), Gate (+)		_	30	mA
	SM12		II			T2 (+) , Gate (-)	_	_	30	
	SM12	2J45	III			T2 (-) , Gate (-)	_	_	30	
			IV			T2 (-) , Gate (+)	I	_		
			- 1			T2 (+), Gate (+)		_	20	
		2G45A	II			T2 (+) , Gate (-)	I	_	20	
	SM12	SM12J45A	III			T2 (-) , Gate (-)		_	20	
						T2 (-) , Gate (+)	I	_		
Peak On-State Voltage		V_{TM}	I _{TM} = 17A		I	_	1.5	V		
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_		V		
Holding Current		lΗ	V _D = 12V, I _{TM} = 1A			_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC		_	_	1.8	°C/W		
Critical Rate of Rise of Off-State Voltage at Commutation SM12G45 SM12J45 SM12G45A SM12J45A			(dv / dt) c	V _{DRM} = 400V		10			V / ue	
			(uv / ut) C	(di / dt) c = - 6.	5A / ms	4	_	_	· V / μs	

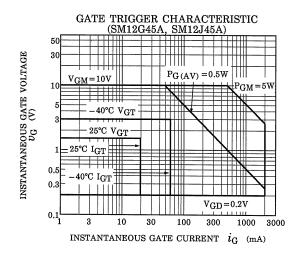
2

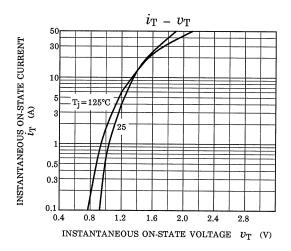
MARKING

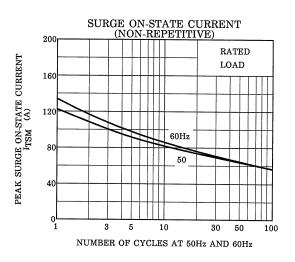


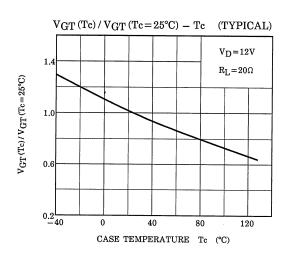
	Part No. (or abbreviation code)	Part No.
*1	M12G45	SM12G45, SM12G45A
	M12J45	SM12J45, SM12J45A
*2	Α	SM12G45A,SM12J45A

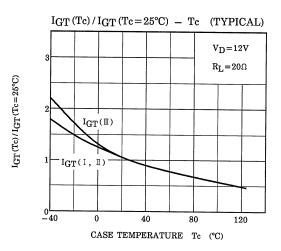


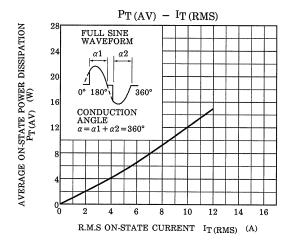


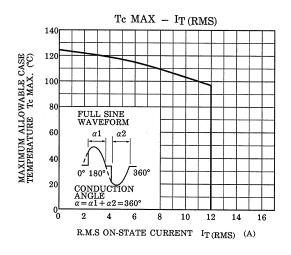


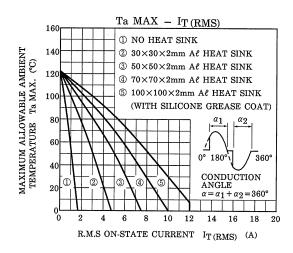


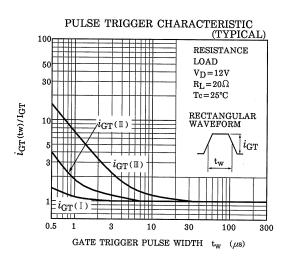


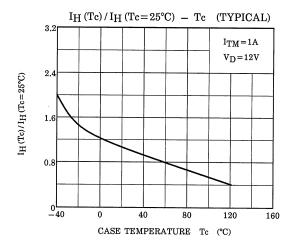


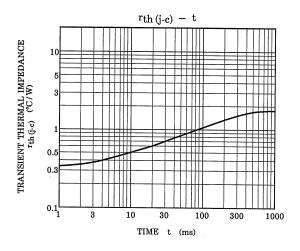












4

RESTRICTIONS ON PRODUCT USE

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patent or patent rights of
 TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.